

isc Silicon NPN Power Transistor

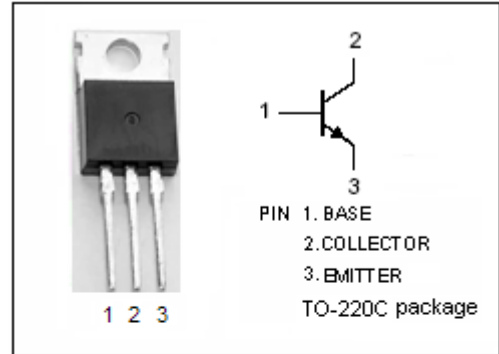
2SD568

DESCRIPTION

- High Collector Current:  $I_C = 7A$
- Low Collector Saturation Voltage  
:  $V_{CE(sat)} = 0.5V(Max) @ I_C = 5A$
- Complement to Type 2SB707

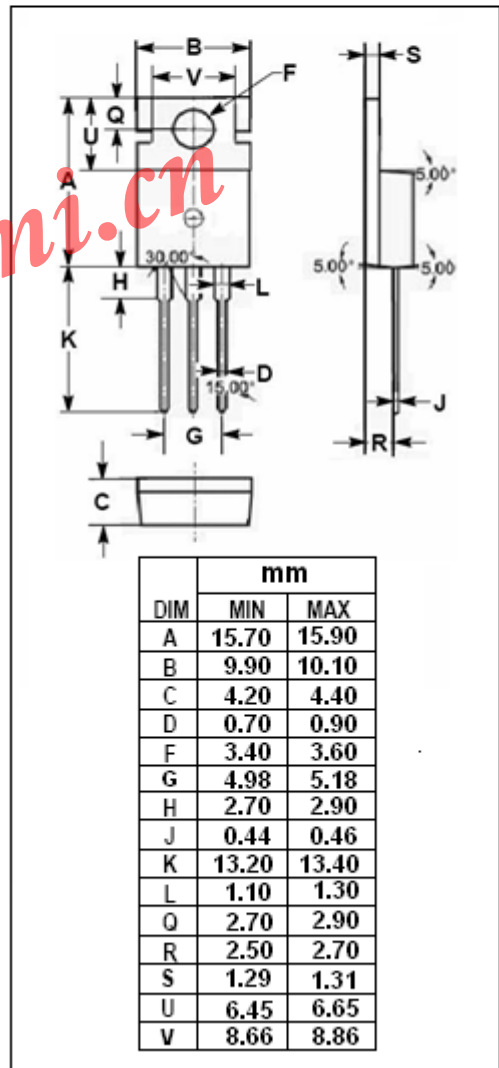
APPLICATIONS

- Designed for low-frequency power amplifiers and low-speed switching applications.



ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	80	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	7	A
$I_{CM}$	Collector Current-Peak	15	A
$I_B$	Base Current-Continuous	3.5	A
$P_C$	Total Power Dissipation @ $T_C=25^{\circ}C$	40	W
	Total Power Dissipation @ $T_a=25^{\circ}C$	2	
$T_J$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-55~150	$^{\circ}C$



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	60			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=0.5\text{A}$			0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=0.5\text{A}$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=60\text{V}; I_E=0$			10	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			10	$\mu\text{A}$
$h_{FE-1}$	DC Current Gain	$I_C=3\text{A}; V_{CE}=1\text{V}$	40		200	
$h_{FE-2}$	DC Current Gain	$I_C=5\text{A}; V_{CE}=1\text{V}$	20			

◆  $h_{FE-1}$  Classifications

M	L	K
40-80	60-120	100-200